## UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO. : 7,247,248 B2 APPLICATION NO. : 10/516927

: July 24, 2007

DATED INVENTOR(S)

: Tee et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 2, Line 56 - Replace "silicon I" with --silicon 1--.

Column 4, Line 27 – Replace "A method of..." with --A method of forming silicon atomic force microscope tips including the steps of:--.

Column 5, Line 22 - Replace "is and electrochemical" with --is an electrochemical--.

Signed and Sealed this

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Fifteenth Day of April, 2008

JON W. DUDAS Director of the United States Patent and Trademark Office